

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
20V	0.45Ω @ V <sub>GS</sub> = 4.5V	0.87A
	0.6Ω @ V <sub>GS</sub> = 2.5V	0.76A

## Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

## Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Load Switch
- Power Management Functions

## Mechanical Data

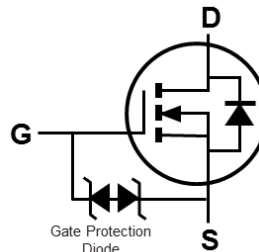
- Case: SOT523
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.002 grams (Approximate)



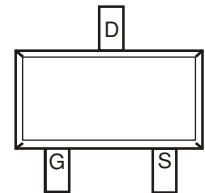
ESD PROTECTED



Top View



Equivalent Circuit



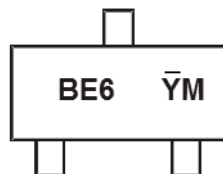
Top View

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2710UT-7	SOT523	3000/Tape & Reel
DMN2710UT-13	SOT523	10000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



BE6 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: H = 2020)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	H	I	J	K	L	M	N	O	P	R	S	T

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DS}$	20	V
Gate-Source Voltage			$V_{GS}$	$\pm 6$	V
Continuous Drain Current (Note 6) $V_{GS} = 4.5\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	$I_D$	0.87	A
		$T_A = +75^\circ\text{C}$		0.7	
Maximum Continuous Body Diode Forward Current (Note 6)			$I_S$	0.65	A
Pulsed Drain Current (10 $\mu\text{s}$ Pulse, Duty Cycle = 1%)			$I_{DM}$	5.6	A

**Thermal Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		$P_D$	0.32	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	395	$^\circ\text{C/W}$
Total Power Dissipation (Note 6)		$P_D$	0.52	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	241	$^\circ\text{C/W}$
Operating and Storage Temperature Range		$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	20	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	100	nA	$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 1.0$	$\mu\text{A}$	$V_{GS} = \pm 4.5\text{V}, V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	0.5	—	1.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	0.14	0.45	$\Omega$	$V_{GS} = 4.5\text{V}, I_D = 600\text{mA}$
		—	0.17	0.6		$V_{GS} = 2.5\text{V}, I_D = 500\text{mA}$
		—	0.22	0.75		$V_{GS} = 1.8\text{V}, I_D = 350\text{mA}$
Diode Forward Voltage	$V_{SD}$	—	0.7	1.2	V	$V_{GS} = 0\text{V}, I_S = 150\text{mA}$
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	$C_{iss}$	—	42	—	pF	$V_{DS} = 16\text{V}, V_{GS} = 0\text{V}$ $f = 1.0\text{MHz}$
Output Capacitance	$C_{oss}$	—	13	—	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	6.5	—	pF	
Gate Resistance	$R_g$	—	1.6	—	k $\Omega$	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Total Gate Charge	$Q_g$	—	0.6	—	nC	$V_{GS} = 4.5\text{V}, V_{DS} = 10\text{V},$ $I_D = 250\text{mA}$
Gate-Source Charge	$Q_{gs}$	—	0.1	—	nC	
Gate-Drain Charge	$Q_{gd}$	—	0.1	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	4.9	—	ns	$V_{DD} = 10\text{V}, V_{GS} = 4.5\text{V},$ $R_L = 47\Omega, R_g = 10\Omega$ $I_D = 200\text{mA}$
Turn-On Rise Time	$t_R$	—	3.1	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	386	—	ns	
Turn-Off Fall Time	$t_F$	—	174	—	ns	
Reverse Recovery Time	$t_{RR}$	—	88	—	ns	$I_F = 1.0\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Reverse Recovery Charge	$Q_{RR}$	—	29	—	nC	$I_F = 1.0\text{A}, di/dt = 100\text{A}/\mu\text{s}$

- Notes:
- Device mounted on FR-4 substrate PC board, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1 inch square copper plate.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

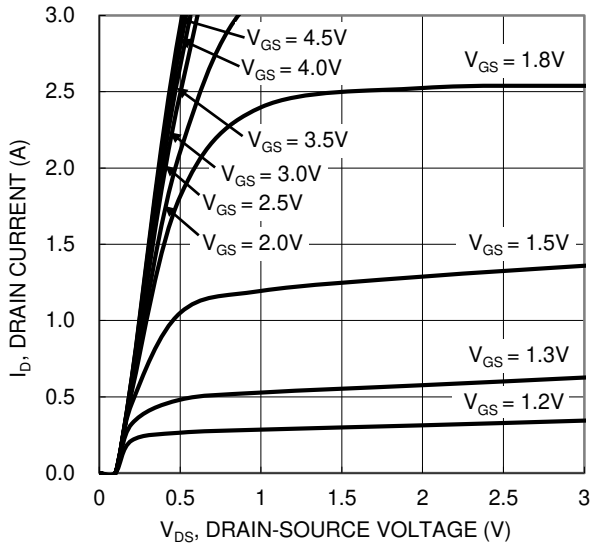


Figure 1. Typical Output Characteristic

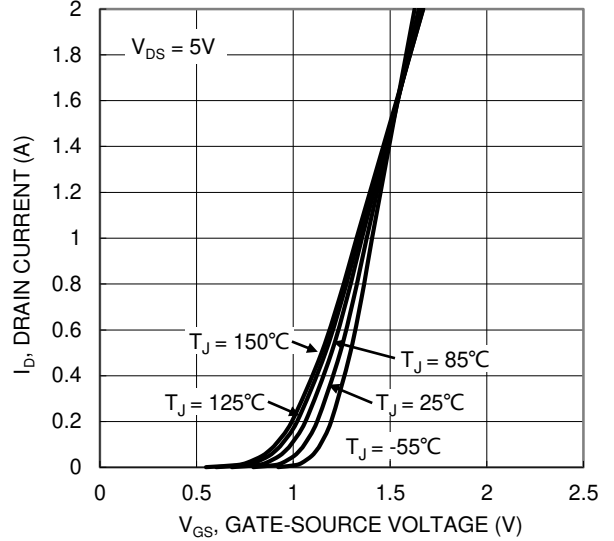


Figure 2. Typical Transfer Characteristic

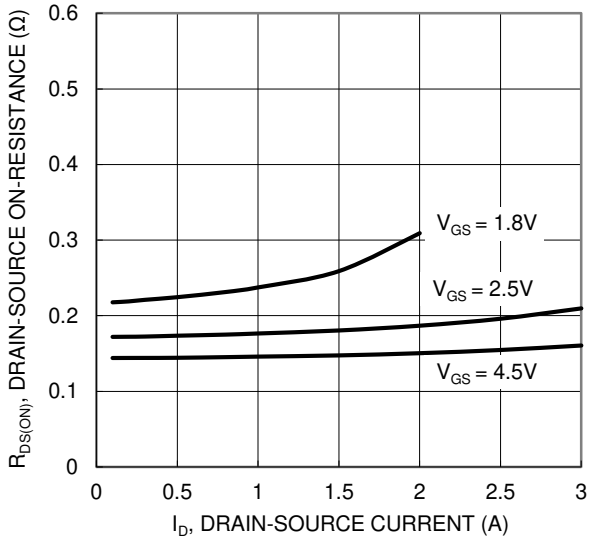


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

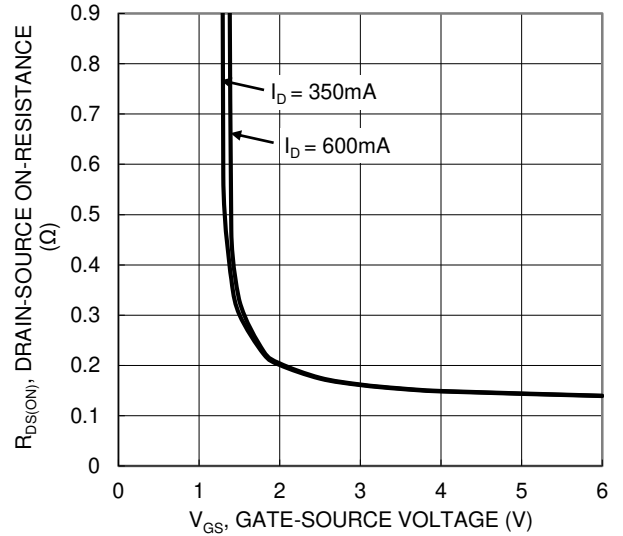


Figure 4. Typical Transfer Characteristic

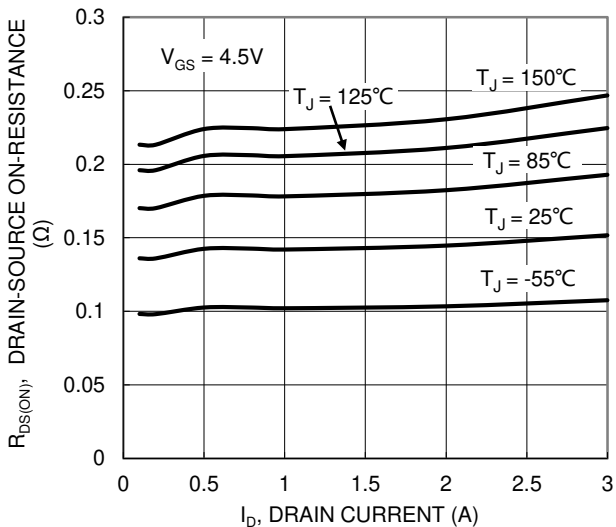


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

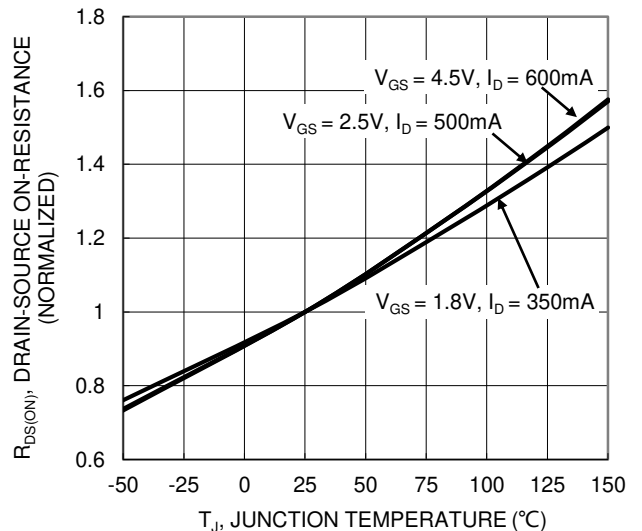


Figure 6. On-Resistance Variation with Temperature

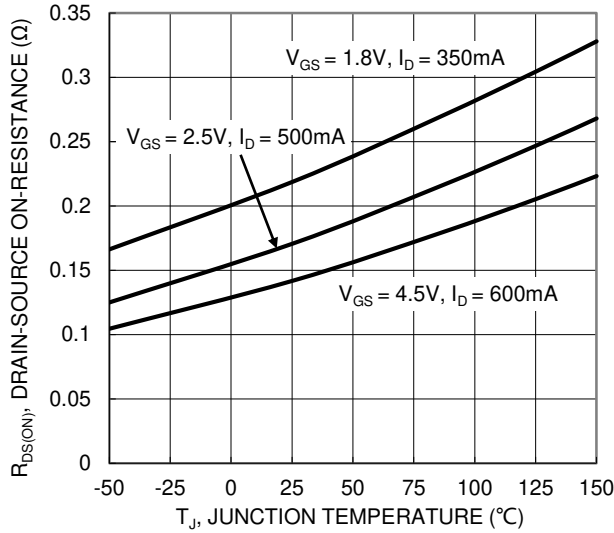


Figure 7. On-Resistance Variation with Temperature

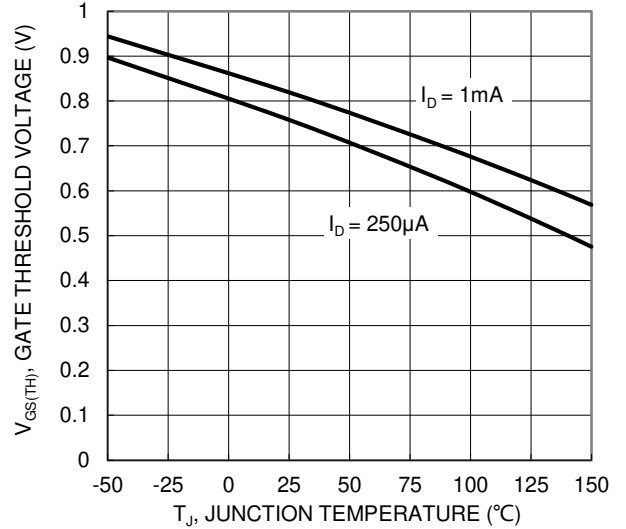


Figure 8. Gate Threshold Variation vs. Junction Temperature

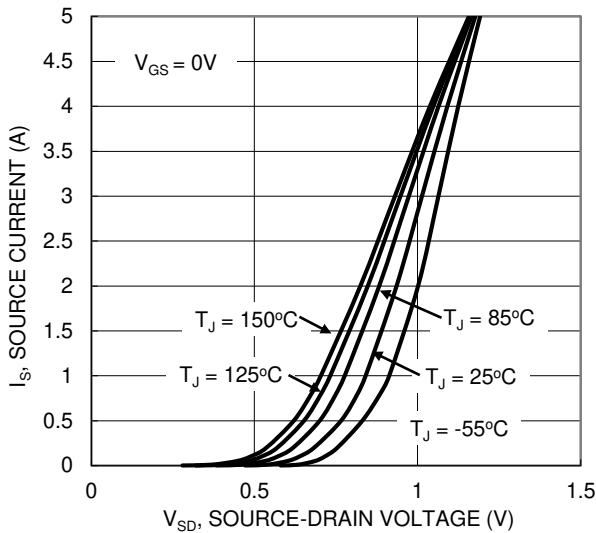


Figure 9. Diode Forward Voltage vs. Current

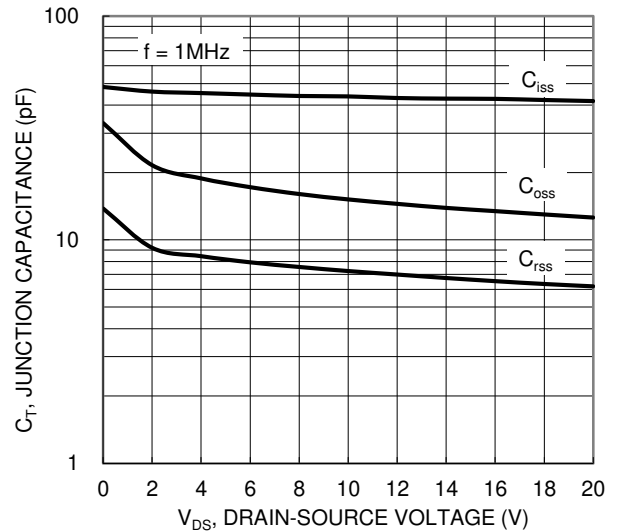


Figure 10. Typical Junction Capacitance

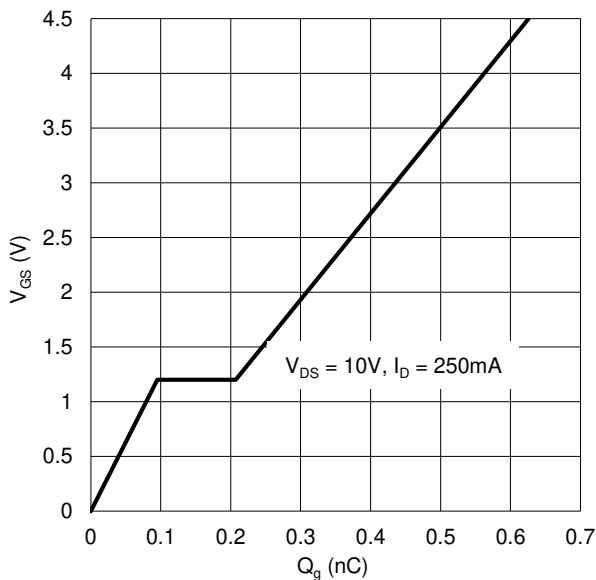


Figure 11. Gate Charge

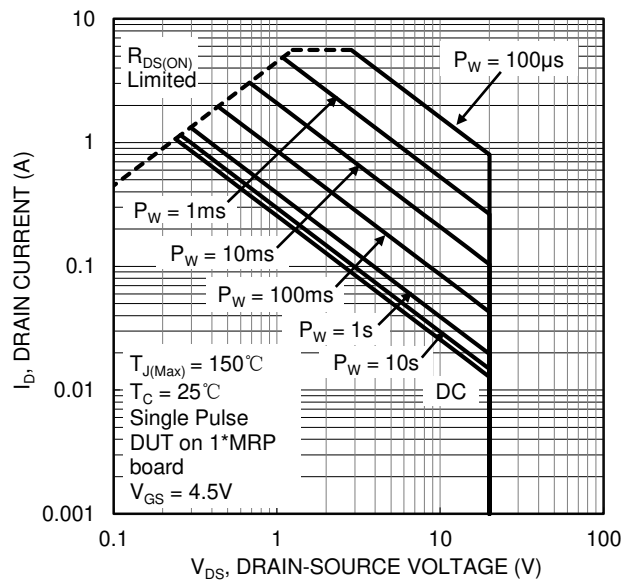


Figure 12. SOA, Safe Operation Area

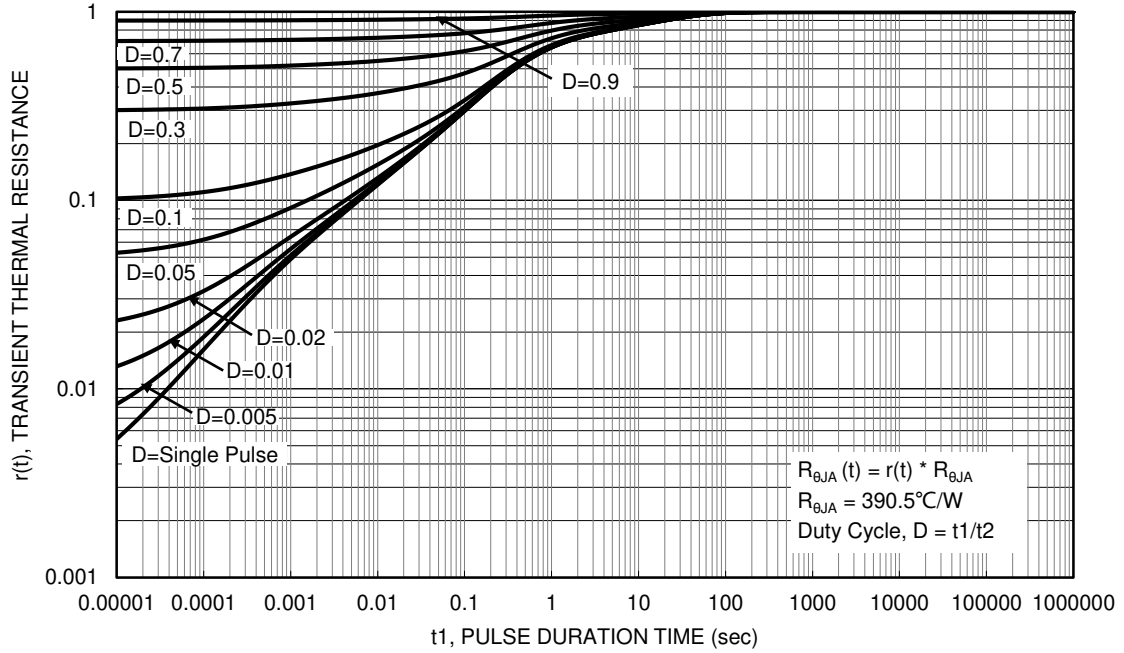
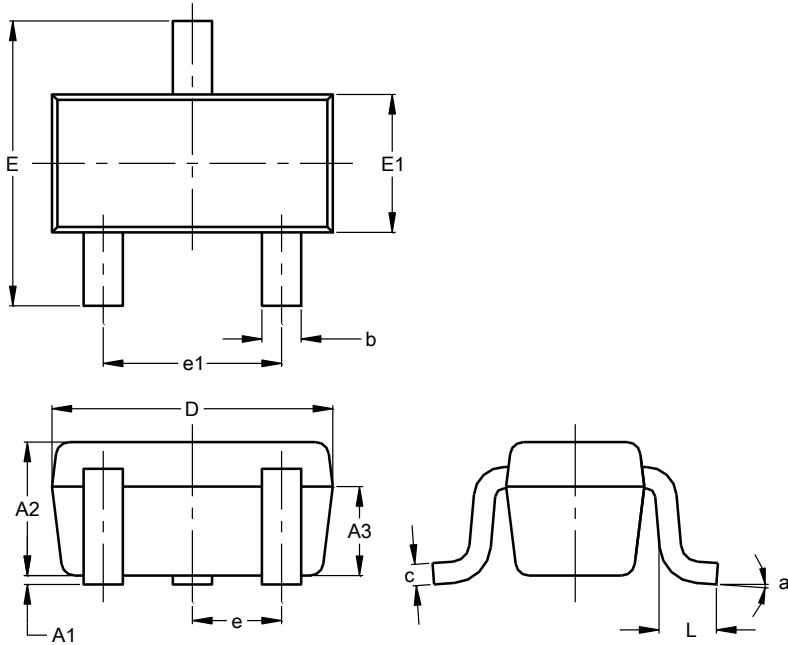


Figure 13. Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT523**

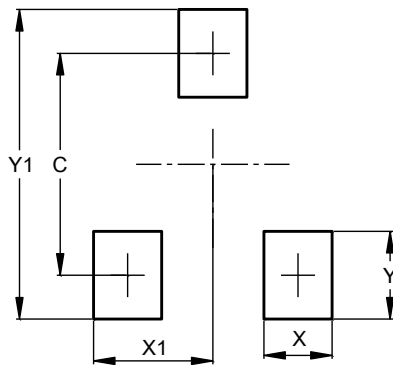


SOT523			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.60	0.80	0.75
A3	0.45	0.65	0.50
b	0.15	0.30	0.22
c	0.10	0.20	0.12
D	1.50	1.70	1.60
E	1.45	1.75	1.60
E1	0.75	0.85	0.80
e	0.50 BSC		
e1	0.90	1.10	1.00
L	0.20	0.40	0.33
a	0°	--	8°
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT523**



Dimensions	Value (in mm)
C	1.29
X	0.40
X1	0.70
Y	0.51
Y1	1.80

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